EHB 122-E - HW-P

a) Operation Regions

PMOS:
$$|V_{ess} - V_T| = |(0-5) - (-0.35)| = 4.05V -> |V_{ess} + p|$$

 $|V_{DS}| = |5 - 0.2| = 4.8V$

Since IVGS-VT | \(IVDS | -> Saturation
4.05 \(4.8 \)

Nuos:
$$|V_{GS}-V_{7}|=|(5-0)-(0,7)|=4.3 \rightarrow V_{Sadm}$$

 $|V_{DS}|=|0,2-0|=0,2$

since 1 Vas - V7 17, 1 Vps 1 -> Linear 4,3 >, 0,2

By using current equations, we can find desired WN value.

$$I_n = I_p$$

156.1006. Wn (1,68) = 48.1006. 3,2.10-6. (16,4025)

$$W_n = \frac{16,4025.48.10^{-6}, 3,2.10^{-6}}{156.10^{-6}, 1,68}$$

b)
$$V_{in} = V_{out} = V_{in}$$

Operation Regions
 $PMOS: |V_{GS} - V_{Tp}| = 4.05 V$
 $|V_{DS}| = |S - V_{out}| = |S - V_{ui}|$
 $|V_{DS}| = |S - V_{out}| = |S - V_{ui}|$
 $|V_{DS}| = |V_{ui}|$
 $|V_{ui} - 0.7|$
 $|V_{ui} - 0.7| = |V_{ui} - V_{ui}|$
 $|V_{ui} - V_{ui}|$

Root 1 -> 1,955 -> |Vu = 1,955 V

Root 2 -> -0,509

C)
$$V_{1n}=0$$
 — Nuos is aft, no current flowing

 $P_{S}=D$ (we could use P_{P} or $P_{P}=P_{P}$)

 $V_{1n}=S-P_{S}=V.P=S-P_{$